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forming an insulating film comprising silicon oxide on said
crystalline semiconductor film by a vapor phase deposition using TEOS;
and
irradiating an intense light to said insulating film in an atmosphere
comprising an oxygen gas.

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35. The method of claim 34 wherein said intense light is an IR light.

36. The method of claim 34 wherein said vapor phase deposition is
performed by a plasma CVD or a low pressured CVD.

37. The method of claim 34 wherein the irradiation of said intense light
is performed in order to reduce an interfacial layer density to 10^{11} cm^{-2} or lower. —

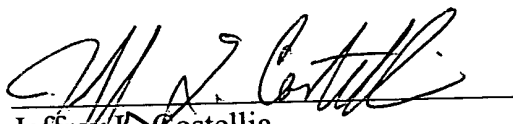
REMARKS

The Office Action of November 21, 2000 was received and carefully reviewed. Claims 1-28 were pending in this application. In response to the species election, Applicants hereby elect Group I directed to claims 1-14 without traverse.

It is also noted that applicants have amended these claims and also added new claims 29-37 for consideration to complete the scope of protection to which Applicants are entitled. It should be noted that these amendments are not made in response to any rejection, and, thus, should not effect the scope of protection afforded these claims, once issued.

In view of the above, elected claims 1-14 and new claims 29-37, as well as claims 15-28, are believed to be in condition for allowance. Should the Examiner deem that any further action by the applicants would be desirable to place this application in even better condition for issue, he is requested to contact the undersigned.

Respectfully submitted,



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1. (Amended) A method for manufacturing a semiconductor device comprising the steps of:
forming a semiconductor film comprising amorphous silicon over a substrate;
crystallizing said semiconductor film by irradiating a laser light; forming an insulating film on the crystallized semiconductor film by a vapor phase deposition; and
[thermal annealing] irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas.
2. (Amended) The method of claim 1 wherein said [thermal annealing step is performed at a temperature from 1000 to 1200] intense light is an IR light.
3. (Amended) The method of claim 1 wherein said vapor phase deposition is performed by a plasma CVD [and] or a low pressured CVD.
4. (Amended) The method of claim 1 wherein [said thermal annealing step] the irradiation of said intense light is performed in order to reduce an interfacial layer density to 10^{11} cm^{-2} or lower.
6. (Amended) A method for manufacturing a semiconductor device comprising the steps of:
forming a semiconductor film comprising amorphous silicon over a substrate;
crystallizing said semiconductor film by irradiating a laser light;
forming an insulating film comprising silicon oxide on the crystallized semiconductor film by a vapor phase deposition; and

[thermal annealing] irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas.

7. (Amended) The method of claim 6 wherein said [thermal annealing step is performed at a temperature from 1000 to 1200] intense light is an IR light.

8. (Amended) The method of claim 6 wherein said vapor phase deposition is performed by a plasma CVD [and] or a low pressured CVD.

9. (Amended) The method of claim 6 wherein [said thermal annealing step] the irradiation of said intense light is performed in order to reduce an interfacial layer density to 10^{11} cm^{-2} or lower.

11. (Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon over a substrate;

crystallizing said semiconductor film by irradiating a laser light;

forming an insulating film comprising silicon oxide on the crystallized semiconductor film by a vapor phase deposition using TEOS;
and

[thermal annealing] irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas [in order to reduce an interfacial layer density to 10^{11} cm^{-2} or lower].

12.. (Amended) The method of claim 11 wherein said [thermal annealing step is performed at a temperature from 1000 to 1200] intense light is an IR light.

13. (Amended) The method of claim 11 wherein said vapor phase deposition is performed by a plasma CVD [and] or a low pressured CVD.